EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	10/761704	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/05 15:04
L2	32113	(surface near channel)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/05 15:04
L3	78	(surface near channel) same (high-k or (high near2 dielectric))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/05 15:05
L4	75	(surface near channel) same (high-k or (high near2 dielectric)) same gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/05 15:13
L5	67	(surface adj channel) same (high-k or (high near2 dielectric)) same gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/05 15:14
L6	5	((surface adj channel) same (high-k or (high near2 dielectric)) same gate).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/05 15:15
L7	24520	"surface channel"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/05 15:16
L8	977	"surface channel" and (high-k or (high near2 dielectric))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/05 15:16
L9	831	"surface channel" and (high-k or (high near2 dielectric)) and gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/05 15:16

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L10	124	("surface channel").clm. and (high-k or (high near2 dielectric)) and gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/05 15:16
L11	48	("surface channel").ti,ab,clm. and (high-k or (high near2 dielectric)).ti,ab,clm. and gate.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/05 15:19
L12	49	"6060755"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/05 15:20
L13	18041	(channel near2 surface).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/05 15:20
L14	61	(channel near2 surface).clm. and (high-k or (high near2 dielectric)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/05 15:24
L15	328	surface near channel near (MOSFET or MOS or (metal adj oxide) or CMOS or (complimentary))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/05 15:30
L16	26	(surface near channel near (MOSFET or MOS or (metal adj oxide) or CMOS or (complimentary))).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/05 15:35
L17	0	"09906533"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/05 15:35
L18	3	"09/906533"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/05 15:35

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L21	21	l20 and well.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/05 15:36
L22	18	l20 and well.clm. and (surface near channel)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/05 15:36
L23	7	l20 and well.clm. and (surface near channel).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/05 15:38
L24	330	well.clm. and (surface near channel).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/05 15:39
L25	85	well.clm. same (surface near channel).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/05 15:40
L26	2707	well same (surface near channel)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/05 15:40
L27	934	well same (surface near channel) same gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/05 15:40
L28	519	well same (surface near channel) same gate same (dielectric or insulating or oxide or insualation or insulator)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/05 15:41
L29	118	well with (surface near channel) with gate with (dielectric or insulating or oxide or insualation or insulator)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/05 15:46
L30	3	well with (surface near channel) with gate with (dielectric or insulating or oxide or insulation or insulator) with (high-k or (high near2 dielectric))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/05 16:36

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L31	22	(surface near channel) with gate with (dielectric or insulating or oxide or insulation or insulator) with (high-k or (high near2 dielectric))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/05 15:49
L32	3	(surface near channel) with gate with (dielectric or insulating or oxide or insulation or insulator) with (high-k or (high near2 dielectric)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/05 15:49
L33	5	(surface near channel) same gate same (dielectric or insulating or oxide or insulation or insulator) same (high-k or (high near2 dielectric)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/05 15:51
L34	15	(surface near channel) same gate same (dielectric or insulating or oxide or insulation or insulator) same (high-k or (high near2 dielectric)) and (channel near5 (deposit or depositing or deposited or deposition))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/05 15:51
L35	8	(surface near channel) same gate same (dielectric or insulating or oxide or insulation or insulator) same (high-k or (high near2 dielectric)) and (channel near2 (deposit or depositing or deposited or deposition))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/05 15:52
L36	3	(surface near channel) same gate same (dielectric or insulating or oxide or insulation or insulator) same (high-k or (high near2 dielectric)) and ((channel or (surface near channel)) near (deposit or depositing or deposited or deposition))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/05 15:53
L37	2549	((channel or (surface near channel)) near (deposit or depositing or deposited or deposition))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/05 15:53
L38	170	((channel or (surface near channel)) near (deposit or depositing or deposited or deposition)) and (high-k or (high near2 dielectric))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/05 15:55

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L39	25	((channel or (surface near channel)) near (deposit or depositing or deposited or deposition)) with ((metal adj oxide) or oxide) and (high-k or (high near2 dielectric))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/05 15:56
L40	25	(((channel or (surface near channel)) near (deposit or depositing or deposited or deposition)) with ((metal adj oxide) or oxide)) and (high-k or (high near2 dielectric))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/05 15:57
L41	57	(((channel or (surface near channel)) near (deposit or depositing or deposited or deposition)) same (indium oxide (In2O3) ZnO RuO ITO or LaX-1SrXCoO3)) and (high-k or (high near2 dielectric))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/05 15:57
L42	5	(((channel or (surface near channel)) near (deposit or depositing or deposited or deposition)) same ((indium adj oxide) or (In2O3) or (ZnO) or (RuO) or ITO or LaX-1SrXCoO3)) and (high-k or (high near2 dielectric))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/05 16:00
L43	5522	(((channel or (surface near channel)) near (deposit or depositing or deposited or deposition)) same ((indium adj oxide) or (In2O3) or (ZnO) or (RuO) or ITO or LaX-1SrXCoO3) or (zinc adj oxide) or (indium near tin near oxide) or (ruthenium near oxide)) and (high-k or (high near2 dielectric))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/05 15:59
L44	5522	(((channel or (surface near channel)) near (deposit or depositing or deposited or deposition)) same ((indium adj oxide) or (In2O3) or (ZnO) or (RuO) or ITO or LaX-1SrXCoO3) or (zinc adj oxide) or (indium near tin near oxide) or (ruthenium near oxide)) and ((high-k or (high near2 dielectric)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/05 15:59

L45	7	(((channel or (surface near channel)) near (deposit or depositing or deposited or deposition)) and (channel near10 ((indium adj oxide) or (In2O3) or (ZnO) or (RuO) or ITO or LaX-1SrXCoO3))) and (high-k or (high near2 dielectric))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/05 16:00
L46	7	(((channel or (surface near channel)) near (deposit or depositing or deposited or deposition)) and (channel near10 ((indium adj oxide) or (zinc adj oxide) or (ruthenium adj oxide) or (indium near tin near oxide) or (In2O3) or (ZnO) or (RuO) or ITO or LaX-1SrXCoO3))) and (high-k or (high near2 dielectric))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/05 16:01
L47	53	(((channel or (surface near channel)) near (deposit or depositing or deposited or deposition)) and (channel near10 ((indium adj oxide) or (zinc adj oxide) or (ruthenium adj oxide) or (indium near tin near oxide) or (In2O3) or (ZnO) or (RuO) or ITO or LaX-1SrXCoO3)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/05 16:02
L48	54	(((channel or (surface near channel)) near (deposit or depositing or deposited or deposition)) and (channel near10 ((indium adj oxide) or (zinc adj oxide) or (ruthenium adj oxide) or (indium near tin near oxide) or (In2O3) or (ZnO) or (RuO) or ("in.sub.2o.sub.3") or ITO or LaX-1SrXCoO3)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/05 16:02
L49	60	(((channel or (surface near channel)) near (deposit or depositing or deposited or deposition)) and (channel near10 ((indium adj oxide) or (zinc adj oxide) or (ruthenium adj oxide) or (indium near tin near oxide) or (In2O3) or (ZnO) or (RuO) or ("in.sub.2o.sub.3") or la or lanthaum or ITO or LaX-1SrXCoO3)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/05 16:03

L50	4	I20 and ((channel near10 ((indium adj oxide) or (zinc adj oxide) or (ruthenium adj oxide) or (indium near tin near oxide) or (In2O3) or (ZnO) or (RuO) or ("in.sub.2o.sub.3") or la or lanthaum or ITO or LaX-1SrXCoO3)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/05 16:05
L51	4	I20 and ((channel near10 ((indium adj oxide) or (zinc adj oxide) or (ruthenium adj oxide) or (indium near tin near oxide) or (In2O3) or (ZnO) or (RuO) or (lanthanum near2 zirconium near2 cobalt near2 oxide) or (indium near titanium near oxide) or ("in.sub. 2o.sub.3") or la or lanthaum or ITO or LaX-1SrXCoO3)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/05 16:06
L52	1517	((channel near10 ((indium adj oxide) or (zinc adj oxide) or (ruthenium adj oxide) or (indium near tin near oxide) or (In2O3) or (ZnO) or (RuO) or (lanthanum near2 zirconium near2 cobalt near2 oxide) or (indium near titanium near oxide) or ("in.sub. 2o.sub.3") or la or lanthaum or ITO or LaX-1SrXCoO3)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/05 16:06
L53	14	((channel near10 ((indium adj oxide) or (zinc adj oxide) or (ruthenium adj oxide) or (indium near tin near oxide) or (In2O3) or (ZnO) or (RuO) or (lanthanum near2 zirconium near2 cobalt near2 oxide) or (indium near titanium near oxide) or ("in.sub. 2o.sub.3") or la or lanthaum or ITO or LaX-1SrXCoO3))) and high-k	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/05 16:24
L54	14	((channel near10 ((indium adj oxide) or (zinc adj oxide) or (ruthenium adj oxide) or (indium near tin near oxide) or (In2O3) or (ZnO) or (RuO) or (lanthanum near2 zirconium near2 cobalt near2 oxide) or (indium near titanium near oxide) or ("in.sub. 2o.sub.3") or la or lanthanum or ITO or LaX-1SrXCoO3))) and high-k	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/05 16:25

L55	0	((channel near10 ((indium adj oxide) or (zinc adj oxide) or (ruthenium adj oxide) or (indium near tin near oxide) or (In2O3) or (ZnO) or (RuO) or (lanthanum near2 zirconium near2 cobalt near2 oxide) or (indium near titanium near oxide) or ("in.sub. 2o.sub.3") or la or lanthanum or ITO or LaX-1SrXCoO3))) and (high-k near2 (high near dielectric near constant))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/05 16:25
L56	53	((channel near10 ((indium adj oxide) or (zinc adj oxide) or (ruthenium adj oxide) or (indium near tin near oxide) or (In2O3) or (ZnO) or (RuO) or (lanthanum near2 zirconium near2 cobalt near2 oxide) or (indium near titanium near oxide) or ("in.sub. 2o.sub.3") or la or lanthanum or ITO or LaX-1SrXCoO3))) and (high-k or (high near dielectric near constant))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/05 16:25
L57	1578	(channel near10 ((indium adj oxide) or InO or (zinc adj oxide) or ZnO or (RuO) or (ruthenium adj oxide) or (indium near titanium near oxide) or ITO or (lanthanum near zirconium near cobalt near oxide) or ("In.sub.2O.sub.3") or (LaX-1SrXCoO3) or la or lanthanum))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/05 16:40
L58	606	(channel near10 ((indium adj oxide) or InO or (zinc adj oxide) or ZnO or (RuO) or (ruthenium adj oxide) or (indium near titanium near oxide) or ITO or (lanthanum near zirconium near cobalt near oxide) or ("In.sub.2O.sub.3") or (LaX-1SrXCoO3)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/05 16:41
L59	187	((form or forming or formed or formation or deposit or depositing or deposited or deposition) near5 channel near10 ((indium adj oxide) or InO or (zinc adj oxide) or ZnO or (RuO) or (ruthenium adj oxide) or (indium near titanium near oxide) or ITO or (lanthanum near zirconium near cobalt near oxide) or ("In.sub.2O.sub.3") or (LaX-1SrXCoO3)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/05 16:42

L60	82	(well same channel near10 ((indium adj oxide) or InO or (zinc adj oxide) or ZnO or (RuO) or (ruthenium adj oxide) or (indium near titanium near oxide) or ITO or (lanthanum near zirconium near cobalt near oxide) or ("In.sub.2O.sub.3") or (LaX-1SrXCoO3)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/05 16:42
L61	3588	257/288.ccls. or 257/410.ccls. or 257/411.ccls. or 257/289.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/05 17:00
L62	4286	257/288.ccls. or 257/410.ccls. or 257/411.ccls. or 257/289.ccls. or 438/215.ccls. or 438/261.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/05 17:00
L63	623	(257/288.ccls. or 257/410.ccls. or 257/411.ccls. or 257/289.ccls. or 438/215.ccls. or 438/261.ccls.) and (high-k or (high near dielectric)) and channel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/05 17:00
L64	227	(257/288.ccls. or 257/410.ccls. or 257/411.ccls. or 257/289.ccls. or 438/215.ccls. or 438/261.ccls.) and (high-k or (high near dielectric)) same channel same gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/05 17:02
L65	38	l64 and (surface near channel)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/05 17:02